

ANALYSIS OF IONIC BONDS IN SEMICONDUCTING $A^I B^{III} C_2^{VI}$
COMPOUNDS

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ABSTRACT

Semiconducting $A^I B^{III} C_2^{VI}$ compounds were obtained using the Bridgeman procedure. Far infrared reflectivity was measured in the range between 40 and 400 cm^{-1} . The experimental data were numerically analysed and ionic bonds in: AgInSe_2 , CuInSe_2 , AgInTe_2 and CuInTe_2 were discussed.

1. INTRODUCTION

Many papers about $A^I B^{III} C_2^{VI}$ compounds have recently been published¹⁾. The main reason for this is the possible use of their specific semiconducting properties for producing light emitting diodes (LED), solar cells, lasers and nonlinear optical elements²⁾. These compounds have a rather wide range of values for energy gaps so that there is a great possibility of choosing a suitable material for making devices. A good deal of work has been published on CuInSe_2 and CuInS_2 . Both these compounds have direct allowed energy gaps³⁾. CuInS_2 , CuGaS_2 , AgGaSe_2 and AgGaS_2 are suitable for making lasers. Successful p-n junctions have also been made from CuInSe_2 and CuInS_2 ^{4,5)}. Lattice reflectivity spectra of CuGaS_2 , AgGaS_2 ^{6,7)}, AgInTe_2 ⁸⁾, AgInSe_2 ⁹⁾ and even solid solutions of CuGaS_2 - CuGaSe_2 have also been studied¹⁰⁾.

In this work we have investigated the lattice vibrations of AgInTe_2 , AgInSe_2 , CuInTe_2 and CuInSe_2 . Also we discuss the consequences of replacing Ag with Cu atoms and Se with Te atoms in the studied compounds.

2. EXPERIMENTAL

Single crystal samples of AgInSe_2 were made using the Bridgeman procedure. Using the same method only crystalline samples were produced of AgInTe_2 , CuInTe_2 and CuInSe_2 compounds. The specimens for optical measurements were cut from ingots. Slices were between 0.5 and 2 mm thick. The samples were then polished on one side using a conventional polishing technique.

The far infrared reflectivity measurements were performed using a Beckman FS 720 Fourier spectrometer. The variation of near nor-

mal incidence reflectivity of CuInSe_2 is given in Figure 1.

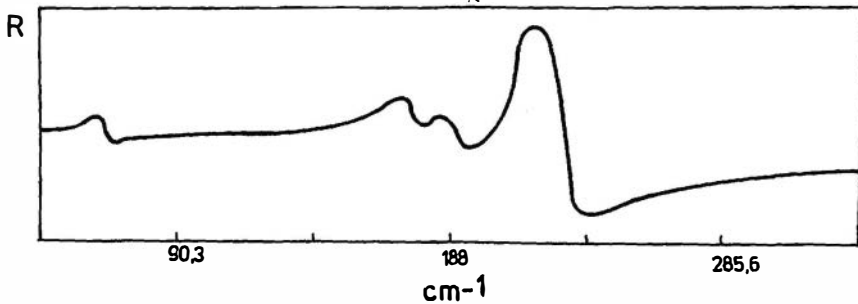


Fig.1. Nonpolarised far infrared reflectivity of CuInSe_2

Four reststrahlen bands occur in the range between 50 and 250 cm^{-1} . The variation of room temperature reflectivity of AgInSe_2 with wavenumber is given in figure 2. The light was polarised in the $\vec{E} \perp \vec{c}$ direction.

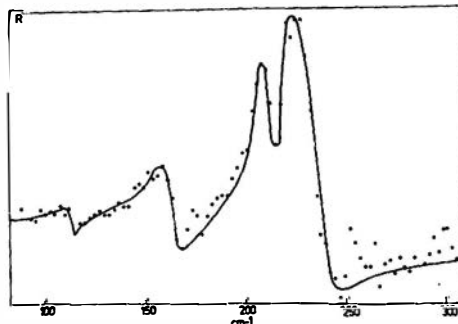


Fig.2. Polarised far infrared reflectivity of AgInSe_2 for $\vec{E} \perp \vec{c}$.

In this figure the experimental values are given with points. The solid line was calculated using the oscillator parameters obtained by numerical analysis, which was carried out with the aid of a fitting procedure according to Gervai's four parameter model¹¹⁾.

The values of transversal (ω_{T0}) and longitudinal (ω_{L0}) optical modes are given in table 1, together with their damping factors (γ_{T0}) and γ_{L0} , respectively) for all four compounds studied.

In figure 3 are given experimental values of the reflectivity versus wavenumber for CuInSe_2 while the broken line represents the theoretical curve which best fits the values of the parameters given in table 1.

The real [$\text{Re}(\text{EPS})(-)$] and imaginary [$\text{Im}(\text{EPS})(--)$] parts of the complex dielectric function for CuInSe_2 are given in figure 4.

TABLE 1. Optical parameters used to fit far infrared reflectivity spectra. Frequencies and damping factors are expressed in units of cm^{-1} .

	AgInSe ₂				AgInTe ₂		CuInSe ₂				CuInTe ₂
	I	II	III	IV		I	II	III	IV		
ϵ_{TO}	113	158	200	219	168	67	175	190	212	145	
ϵ_{LO}	114	166	214	239	184	70	183	197	236	179	
γ_{TO}	5	10	2.3	2.3	4.13	10	12	10	0.7	21.5	
γ_{LO}	4	9	9	9	4.13	15	14	15	13	32.8	
ϵ_{∞}	12				9.84		16				14.8

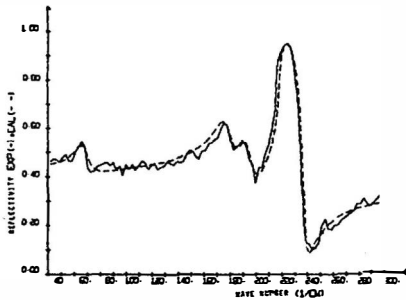


Fig.3. Experimental far infrared reflectivity (solid line) of CuInSe₂. Broken line represents theoretical curve.

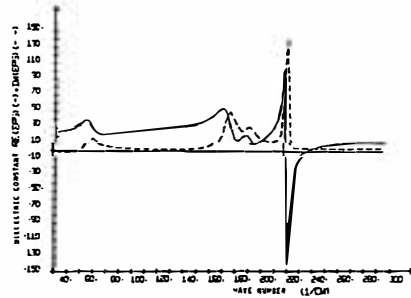


Fig.4. The real and imaginary parts of the complex dielectric function.

4. ANALYSIS AND DISCUSSION OF RESULTS

As far as we know, our experimental and numerical data could be compared with the only literature data published for CuInSe₂⁷⁾. We have also observed four infrared active modes, but there are differences in the position of transverse and longitudinal optical frequencies for first, second and fourth oscillators. Gan et al⁷⁾ did not determine the values of damping factors so that we cannot compare our values with any literature data. It is interesting to emphasize that Gan et al⁷⁾ could not distinguish longitudinal from transverse optical modes for the first two oscillators. In our case we obtained the values 67 and 70 for the first and 175 and 183 for the second oscillator and that is what one would expect.

We have also checked the composition of our CuInSe₂ samples using X-ray analysis, and the obtained values for the lattice para-

meters were in good agreement with the literature values.

As far as we know there are no previous studies of lattice vibrations in AgInSe_2 . Our experimental data where we have observed four active infrared modes for \tilde{E}_{1c}^+ , are in good agreement with the group theory prediction⁷⁾.

Knowing that the atomic weights of Cu and Ag are rather big, one would expect that the oscillator frequencies are much lower for AgInSe_2 samples compared with CuInSe_2 . In practice this is not the case and even more some AgInSe_2 modes are moved towards higher frequencies. These results are in agreement with the literature data obtained by Koschel et al⁶⁾ for CuGaS_2 and AgGaS_2 . This means that the role of either Ag or Cu atoms in forming ionic bonds is relatively small. If, on the contrary, we compare the positions of the optical modes for CuInS_2 and CuGaS_2 it is obvious that the changes in position of their optical modes is in agreement with the differences in the atomic weights of indium and gallium.

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